

L Number	Hits	Search Text	DB	Time stamp
-	119	257/625.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 12:38
-	113	257/625.cccls. and (@ad<20010501)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 12:48
-	191	438/740.cccls. and (@ad<20010501)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 12:49
-	115	(438/740.cccls. and (@ad<20010501)) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 12:52
-	59	257/459.cccls. and (tan or wn or tasn or sin or tungsten or tantalum or (etch adj stop))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 13:17
-	174	438/459.cccls. and (tan or wn or tasn or sin or tungsten or tantalum or (etch adj stop))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 14:02
-	3135	(wafer or (semiconductor adj substrate)) near (trench or cavity or recess)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 14:01
-	5503	(wafer or (semiconductor adj substrate)) near (via or trench or cavity or recess)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 14:01
-	5	(plastic adj mold) near epoxy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 14:16
-	36	((wafer or (semiconductor adj substrate)) near (via or trench or cavity or recess) ) and ((trench or cavity or recess or via) near (tan or wn or tasn or sin or tungsten or tantalum or (etch adj stop)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 14:22